RENESAS

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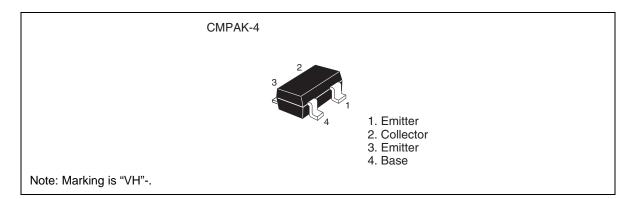
Silicon NPN Epitaxial High Frequency Low Noise Amplifier

REJ03G0129-0200Z (Previous ADE-208-978(Z)) Rev.2.00 Oct.21.2003

Features

- High gain bandwidth product f_T = 28 GHz typ.
- High power gain and low noise figure ; PG = 18 dB typ., NF = 1.2 dB typ. at f = 1.8 GHz

Outline





Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

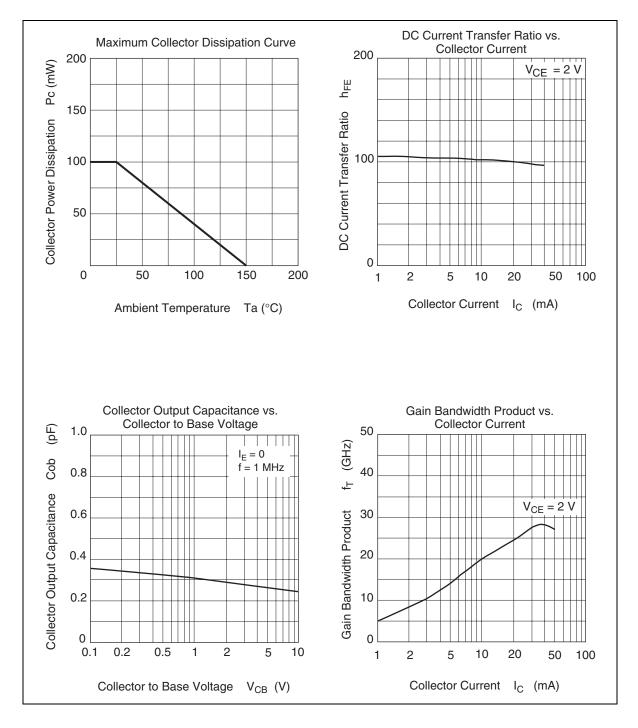
Item	Symbol	Ratings	Unit	
Collector to base voltage	V _{CBO}	10	V	
Collector to emitter voltage	V _{CEO}	3.5	V	
Emitter to base voltage	V _{EBO}	0.8	V	
Collector current	Ic	35	mA	
Collector power dissipation	Pc	100	mW	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Electrical Characteristics

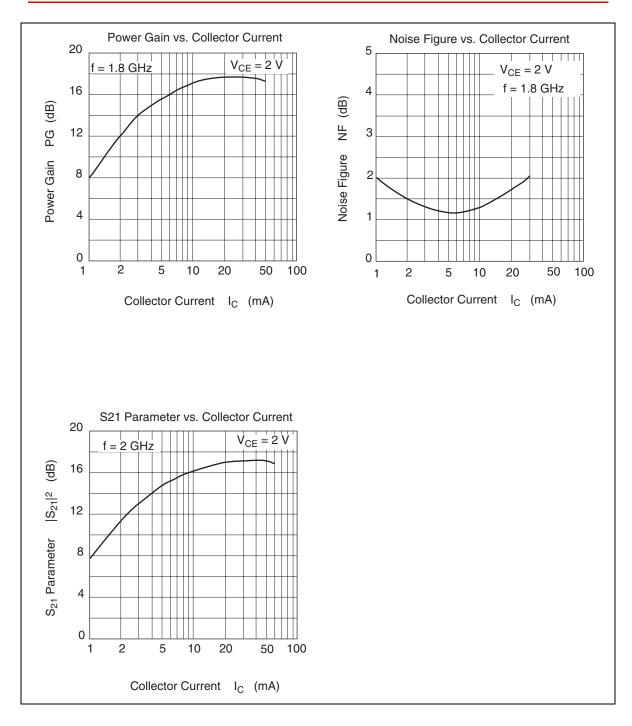
 $(Ta = 25^{\circ}C)$

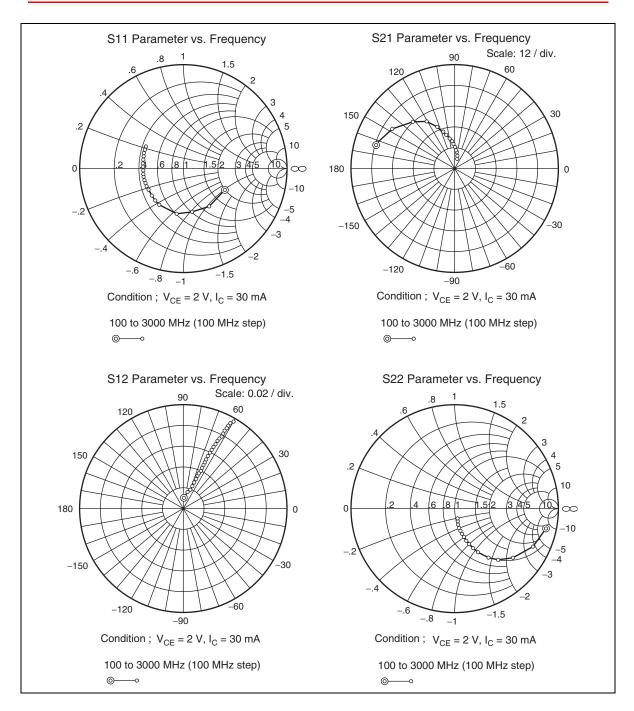
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Collector to base breakdown voltage	V _{(BR)CBO}	10	—	_	V	$I_C = 10 \; \mu A$, $I_E = 0$
Collector cutoff current	I _{CBO}	_	_	1	μA	$V_{CB}=8\ V$, $I_{E}=0$
Collector cutoff current	I _{CEO}	_	_	1	μA	V_{CE} = 3 V , R_{BE} = ∞
Emitter cutoff current	I _{EBO}	_	_	10	μΑ	V_{EB} = 0.8 V , I_{C} = 0
DC current transfer ratio	h _{FE}	80	120	160		V_{CE} = 2 V , I_{C} = 20 mA
Collector output capacitance	Cob	_	0.3	0.6	pF	$V_{CB} = 2 V$, $I_E = 0$ f = 1 MHz
Gain bandwidth product	f _T	25	28	—	GHz	$V_{CE} = 2 V$, $I_C = 30 mA$ f = 2 GHz
Power gain	PG	14	18	—	dB	$V_{CE} = 2 V, I_C = 30 mA$ f = 1.8 GHz
Noise figure	NF		1.2	1.6	dB	$V_{CE} = 2 V$, $I_C = 5 mA$ f = 1.8 GHz

Main Characteristics











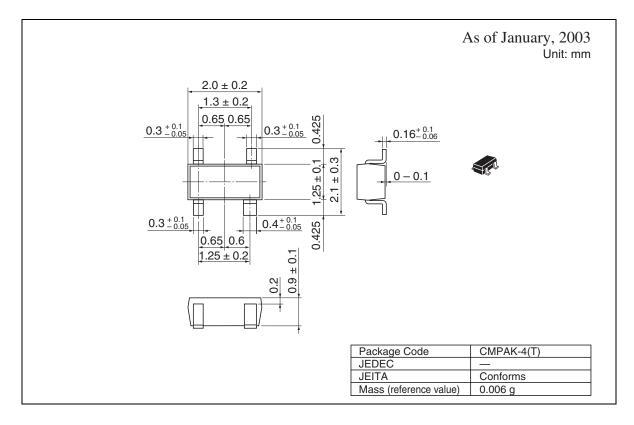
S parameter

 $(V_{CE}$ = 2 V, I_{C} = 30 mA, Zo = 50 Ω)

	S11		S21		S12		S22	
f (MHz)	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.445	-27.3	46.66	163.5	0.0055	83.8	0.904	-12.9
200	0.447	-54.4	42.27	147.1	0.0115	78.6	0.846	-26.8
300	0.439	-78.7	36.16	133.0	0.0165	73.6	0.750	-39.3
400	0.432	-98.8	30.59	122.2	0.0207	68.8	0.650	-48.8
500	0.424	-112.8	25.84	114.5	0.0246	67.1	0.561	-55.9
600	0.414	-124.3	22.15	108.9	0.0277	66.1	0.487	-61.4
700	0.407	-133.4	19.22	104.4	0.0307	65.0	0.426	-65.3
800	0.398	-141.5	16.94	100.8	0.0335	65.3	0.376	-68.6
900	0.390	-147.9	15.05	97.7	0.0372	64.4	0.335	-70.7
1000	0.386	-154.1	13.63	95.3	0.0398	65.1	0.301	-72.5
1100	0.381	-159.0	12.45	93.3	0.0420	65.2	0.273	-73.7
1200	0.377	-164.0	11.48	91.3	0.0452	65.0	0.250	-74.5
1300	0.371	-167.8	10.60	89.6	0.0480	64.5	0.229	-74.9
1400	0.370	-171.8	9.84	87.7	0.0509	64.7	0.213	-75.1
1500	0.367	-175.7	9.23	86.1	0.0535	64.3	0.197	-75.2
1600	0.368	-178.8	8.66	84.7	0.0567	64.1	0.186	-74.7
1700	0.370	178.0	8.16	83.4	0.0595	64.4	0.173	-74.7
1800	0.360	174.7	7.72	82.2	0.0623	64.3	0.164	-74.0
1900	0.365	172.0	7.33	80.8	0.0651	64.0	0.156	-73.6
2000	0.365	168.9	6.95	79.4	0.0682	63.8	0.148	-72.7
2100	0.362	166.8	6.66	78.2	0.0709	63.1	0.142	-72.0
2200	0.372	164.1	6.35	77.0	0.0737	63.0	0.135	-71.3
2300	0.370	160.9	6.08	75.6	0.0764	62.3	0.130	-70.8
2400	0.372	159.0	5.86	74.6	0.0795	62.3	0.125	-69.9
2500	0.378	156.6	5.64	73.5	0.0824	62.0	0.121	-68.7
2600	0.370	154.5	5.42	72.3	0.0848	61.6	0.117	-68.5
2700	0.382	152.2	5.24	71.3	0.0874	61.7	0.113	-67.1
2800	0.388	150.7	5.03	70.3	0.0906	60.7	0.109	-66.8
2900	0.387	147.6	4.86	69.0	0.0928	61.0	0.105	-65.7
3000	0.388	146.9	4.72	67.9	0.0964	59.7	0.102	-65.5



Package Dimensions





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Renesas Technology Europe Limited.

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, United Kingdom Tel: <44> (1628) 585 100, Fax: <44> (1628) 585 900

Renesas Technology Europe GmbH Dornacher Str. 3, D-85622 Feldkirchen, Germany Tel: <49> (89) 380 70 0, Fax: <49> (89) 929 30 11

Renesas Technology Hong Kong Ltd. 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2375-6836

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Renesas Technology (Shanghai) Co., Ltd. 26/F., Ruijin Building, No.205 Maoming Road (S), Shanghai 200020, China Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd. 1, Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

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